Mingda Zhu

List of Publications by Year in Descending Order

24 papers	1,037 citations	13 h-index	26 g-index
26 ext. papers	1,209 ext. citations	3.8 avg, IF	3.71 L-index

#	Paper	IF	Citations
24	Distributed polarization-doped GaN p□ diodes with near-unity ideality factor and avalanche breakdown voltage of 1.25 kV. *Applied Physics Letters*, **2022**, 120, 122111	3.4	0
23	Realization of GaN PolarMOS using selective-area regrowth by MBE and its breakdown mechanisms. *Japanese Journal of Applied Physics*, **2019**, 58, SCCD15	1.4	12
22	Development of GaN Vertical Trench-MOSFET With MBE Regrown Channel. *IEEE Transactions on Electron Devices*, **2018**, 65, 2558-2564	2.9	32
21	Activation of buried p-GaN in MOCVD-regrown vertical structures. *Applied Physics Letters*, **2018**, 113, 062105	3.4	25
20	Strained GaN quantum-well FETs on single crystal bulk AlN substrates. *Applied Physics Letters*, **2017**, 110, 063501	3.4	34
19	Electron mobility in polarization-doped Al0-0.2GaN with a low concentration near 1017 cm□. *Applied Physics Letters*, **2017**, 110, 182102	3.4	8
18	GaN vertical nanowire and fin power MISFETs **2017**,		5
17	600 V GaN vertical V-trench MOSFET with MBE regrown channel **2017**,		10
16	1.1-kV Vertical GaN p-n Diodes With p-GaN Regrown by Molecular Beam Epitaxy. *IEEE Electron Device Letters*, **2017**, 38, 1071-1074	4.4	50
15	Ultralow-Leakage AlGaN/GaN High Electron Mobility Transistors on Si With Non-Alloyed Regrown Ohmic Contacts. *IEEE Electron Device Letters*, **2016**, 37, 16-19	4.4	26
14	1.7-kV and 0.55- $text{m}Omega cdot text {cm}^{2}$ GaN p-n Diodes on Bulk GaN Substrates With Avalanche Capability. *IEEE Electron Device Letters*, **2016**, 37, 161-164	4.4	125
13	Comparing buffer leakage in PolarMOSH on SiC and free-standing GaN substrates **2016**,		1
12	High-voltage polarization-induced vertical heterostructure p-n junction diodes on bulk GaN substrates **2015**,		3
11	Dual optical marker Raman characterization of strained GaN-channels on AlN using AlN/GaN/AlN quantum wells and 15N isotopes. *Applied Physics Letters*, **2015**, 106, 041906	3.4	10
10	Unique opportunity to harness polarization in GaN to override the conventional power electronics figure-of-merits **2015**,		5
9	Near unity ideality factor and Shockley-Read-Hall lifetime in GaN-on-GaN p-n diodes with avalanche breakdown. *Applied Physics Letters*, **2015**, 107, 243501	3.4	117
8	High breakdown single-crystal GaN p-n diodes by molecular beam epitaxy. *Applied Physics Letters*, **2015**, 107, 232101	3.4	44

7	. *IEEE Electron Device Letters*, **2015**, 36, 375-377	4.4	126
6	AlGaN/GaN HEMTs on Si by MBE with regrown contacts and fT = 153 GHz. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 887-889		8
5	Two-dimensional electron gases in strained quantum wells for AlN/GaN/AlN double heterostructure field-effect transistors on AlN. *Applied Physics Letters*, **2014**, 104, 193506	3.4	35
4	GaN lateral PolarSJs: Polarization-doped super junctions **2014**,		2
3	Terahertz imaging employing graphene modulator arrays. *Optics Express*, **2013**, 21, 2324-30	3.3	85
2	Extraordinary control of terahertz beam reflectance in graphene electro-absorption modulators. *Nano Letters*, **2012**, 12, 4518-22	11.5	187
1	Efficient terahertz electro-absorption modulation employing graphene plasmonic structures. *Applied Physics Letters*, **2012**, 101, 261115	3.4	86